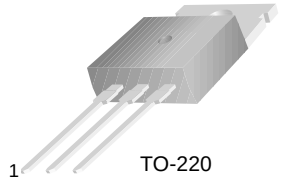
FAIRCHILD
SEMICONDUCTOR TM

KSD362

B/W TV Horizontal Deflection Output

- Collector-Base Voltage : V_{CBO}=150V
- Collector Current : I_C=5A
- Collector Dissipation : P_C=40W(T_C=25°C)



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1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current	5	A
P_C	Collector Dissipation (T_C=25°C)	40	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 1mA, I_E = 0	150			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 2mA, R_{BE} = ∞	70			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 1mA, I_C = 0	8			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 100V, I_E = 0			20	μA
h_{FE}	DC Current Gain	V_{CE} = 5V, I_C = 5A	20		140	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 5A, I_B = 0.5A			1	V
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = 5A, I_B = 0.5A			1.5	V
f_T	Current Gain Bandwidth Product	V_{CE} = 5V, I_C = 0.5A		10		MHz

h_{FE} Classification

Classification	N	R	O
h_{FE}	20 ~ 50	40 ~ 80	70 ~ 140

Typical Characteristics

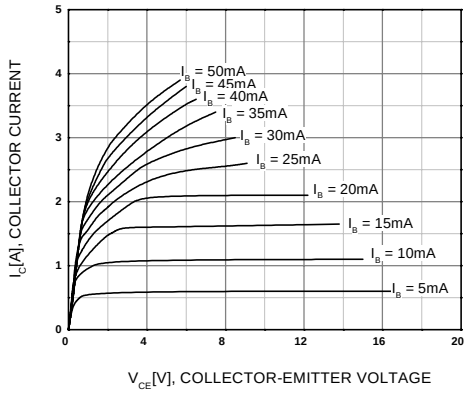

Figure 1. Static Characteristic

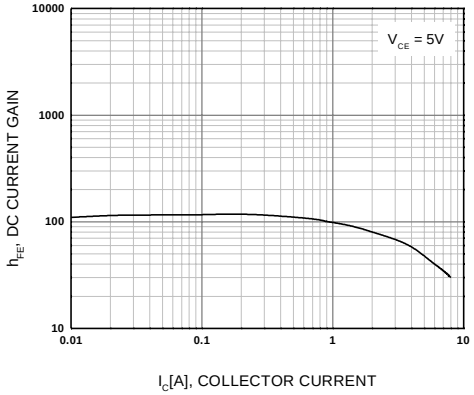

Figure 2. DC current Gain

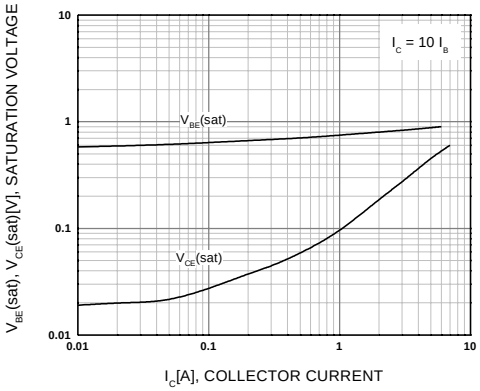

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

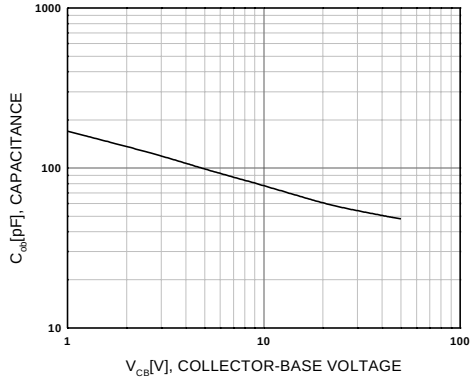

Figure 4. Collector Output Capacitance

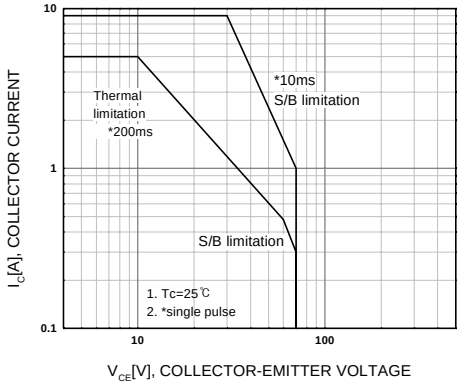

Figure 5. Safe Operating Area

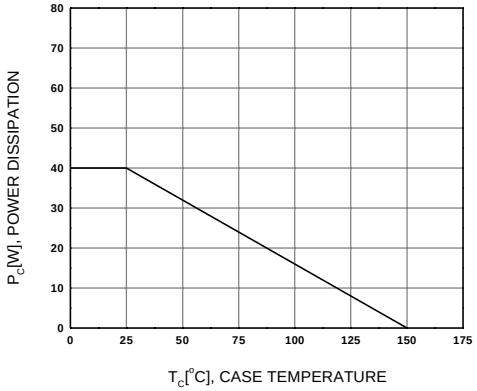

Figure 6. Power Derating

Package Demensions

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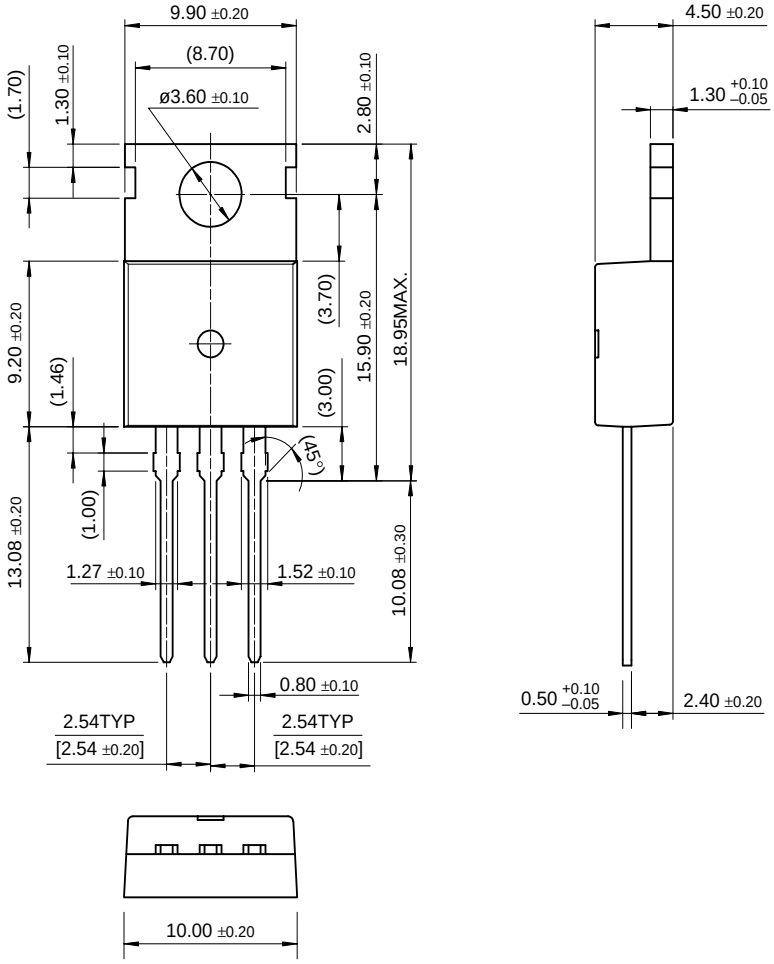

Dimensions in Millimeters

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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KSD362
NPN Epitaxial Silicon Transistor

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Features

- Collector-Base Voltage: V_{CBO}=150V
- Collector Current: I_C=5A
- Collector Dissipation: P_C=40W (T_C=25°C)

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Applications

B/W TV Horizontal Deflection Output

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSD362RTU	Full Production	$0.353	TO-220	3	RAIL
KSD362N	Full Production	$0.353	TO-220	3	BULK
KSD362R	Full Production	$0.353	TO-220	3	BULK

* 1,000 piece Budgetary Pricing

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